

MICRON.0030



PATENT

A

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Pierre C. Fazan et al.) Group Art Unit Unknown
App. No. : 09/037,945)
Filed : March 10, 1998)
For : STREAMLINED FIELD ISOLATION)
PROCESS)
Examiner : Unknown)

3/A
5/6/99
J. R. R.

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Prior to examination on the merits of the above-referenced patent application, please amend the application as indicated below.

IN THE CLAIMS:

Please cancel Claims 5-7 and 10.

1. (Amended) A **[field isolation]** process of forming an integrated circuit, comprising:
growing a silicon dioxide field isolation region on a semiconductor wafer by means
of a hydrogen-free oxidant at a pressure less than about 30 atm; and
forming a gate oxide without a prior sacrificial oxidation.

2. (Amended) The process of Claim 1, wherein the oxidant **[comprises substantially only]** consists essentially of oxygen.

3. (Amended) The process of Claim 1, **[further comprising]** wherein forming the field isolation region comprises exposing the semiconductor **[wafer]** substrate to the oxidant at an oxidant partial pressure greater than 5 atm.

06/19/1998 MICRON 00000125 09037945

01-FC:102

82.00 00